P3D06004T2 650V SiC SBD

 $V_{RRM} = 650 \text{ V}$ Qc = 8.03 nG $I_F(\leq 160^{\circ}\text{C}) = 4 \text{ A}$ $V_F = 1.5 \text{ V}$

SiC SBD P3D06004T2 650V SiC Schottky Diode

2

Features

- Qualified to AEC-Q101
- Ultra-Fast Switching
- Zero Reverse Recovery Current
- High-Frequency Operation
- Positive Temperature Coefficient on V_F
- High Surge Current
- 100% UIS tested

TO-220-2

Cathode	1
Anode	2



Benefits

- Improve System Efficiency
- Reduction of Heat Sink Requirement
- Essentially No Switching Losses
- Parallel Devices Without Thermal Runaway



Applications

- Consumer SMPS
- Boost Diodes in PFC or DC/DC Stages
- AC/DC Converters



Order Information

Part Number	Package	Marking
P3D06004T2	TO-220-2	P3D06004T2

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1. Maximum Ratings

At T_J = 25°C, unless specified otherwise

Parameter	Symbol	Value	Unit	Test condition
Repetitive Peak Reverse Voltage	V _{RRM}	650	V	T _C = 25℃
Surge Peak Reverse Voltage	V _{RSM}	650	V	T _C = 25°C
DC Blocking Voltage	V _R	650	V	T _C = 25°C
Forward Current	I _F	15 8 4	A	$T_C = 25^{\circ}C$ $T_C = 125^{\circ}C$ $T_C = 160^{\circ}C$
Repetitive Peak Forward Surge Current	I _{FRM}	26 14	А	T_C = 25°C, t_p = 10ms T_C = 125°C, t_p = 10ms
Non-Repetitive Forward Surge Current	I _{FSM}	30 29	А	T_{C} = 25°C, t_{p} = 10ms T_{C} = 125°C, t_{p} = 10ms
Non-Repetitive Forward Surge Current	I _{F, MAX}	332 337	Α	T_C = 25°C, t_p = 10 μ s T_C = 125°C, t_p = 10 μ s
Power Dissipation	P _{tot}	81	W	T _C = 25°C
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +175	°C	
TO-220 Mounting Torque M3 Screw	T_{orq}	1 8.8	Nm Ibf-in	

2. Thermal Characteristics

Parameter	Symbol	Values	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.85	°C/W

3. Electrical Characteristics

At T_J= 25°C, unless specified otherwise

			Values			Test condition						
Parameter	Symbol	Min.	Тур.	Max.	Unit							
Famusard Valtage	V	,	1.5	1.7	.,			I _F = 4A, T _J = 25°C				
Forward Voltage	V _F	/	1.8	/	V	I _F = 4A, T _J = 175°C						
Devenue Comment		,	1	20		V _R = 650V, T _J = 25°C						
Reverse Current	I _R	/	48	/	μΑ	V _R = 650V, T _J = 175°C						
			145			V_R = 0V, T_J = 25°C f= 1MHz						
Total Capacitance	C	С	С	С	С	С	С		15.7	/ pF		V _R = 200V, T _J = 25°C f= 1MHz
			12.2			V _R = 400V, T _J = 25°C f= 1MHz						
Total Capacitive Charge	Q_{C}	/	8.03	/	nC	$V_R = 400V, I_F = 4A$ $T_J = 25^{\circ}C$						
Capacitance Stored Energy	E _C	/	1	/	μJ	V _R = 400V						

4. Typical Performance

At T_J= 25°C, unless specified otherwise

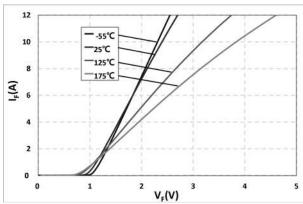


Fig. 1 Typical Forward Characteristics $I_F = f(V_F)$; $T_J = -55^{\circ}C$, 25°C, 125°C, 175°C

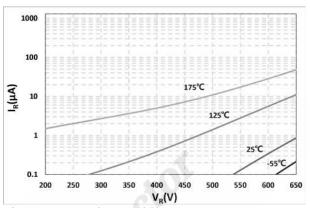


Fig. 2 Reverse Characteristics $I_R=f(V_R)$; $T_J=-55$ °C, 25°C, 125°C, 175°C

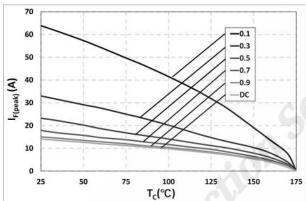


Fig. 3 Current Derating

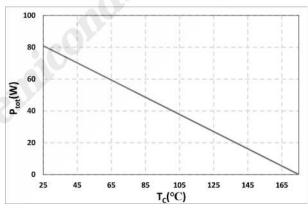


Fig. 4 Typical Power Derating $P_{tot} = f(T_C)$

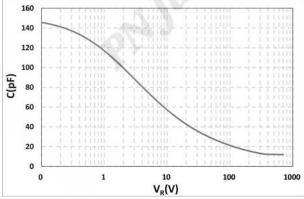


Fig. 5 Typical Total Capacitance C=f(V_R)

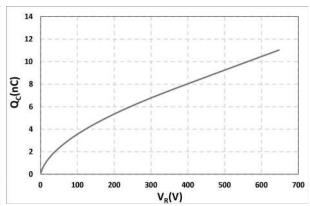
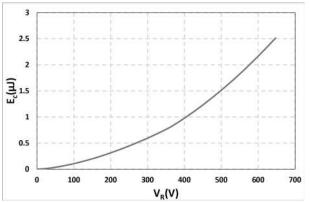


Fig. 6 Typical Total Capacitive Charge $Q_C = f(V_R)$





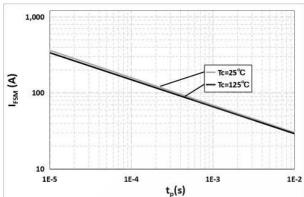


Fig. 7 Capacitance Stored Energy $E_C = f(V_R)$

Fig. 8 Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

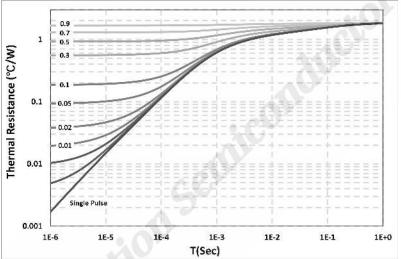
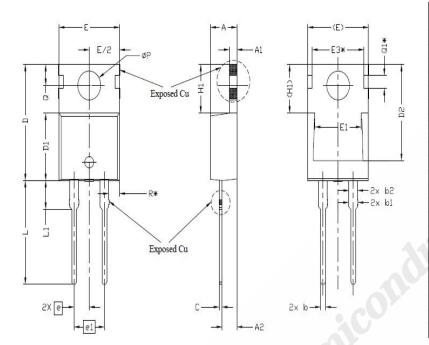


Fig. 9 Transient Thermal Impedance

5. Package Outlines



OVA IDOL		NOTES		
SYMBOL -	MIN.	NOM.	MAX.	NOTES
Α	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
С	0.40	0.50	0.50 0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.63	12.73	12,83	5
Е	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E3*		8.70REF.		
е		2.54BSC		
e1		5.08BSC		
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4,00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*		1.73REF.		
R*	1.82REF.			

Drawing and Dimensions



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